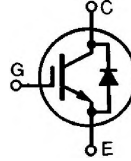


HiPerFAST™ IGBT with Diode

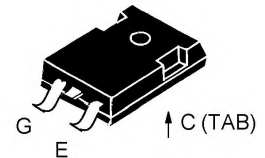
	V_{CES}	I_{C25}	$V_{CE(sat)}$
IXSH 24N60U1 / IXSH 24N60U1S	600 V	48 A	2.2 V
IXSH 24N60AU1 / IXSH 24N60AU1S	600 V	48 A	2.7 V

Short Circuit SOA Capability

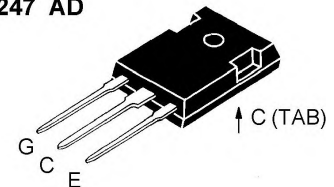


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1\text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	48	A
I_{C90}	$T_C = 90^\circ\text{C}$	24	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	96	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 10\ \Omega$ Clamped inductive load, $L = 100\ \mu\text{H}$	$I_{CM} = 48$ @ $0.8\ V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = 15\text{ V}$, $V_{CE} = 360\text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 82\ \Omega$, non-repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	150	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum Lead and Tab temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque, TO-247	1.13/10	Nm/lb.in.
Weight	TO-247 SMD	4	g
	TO-247 AD	6	g

TO-247 SMD (...S)



TO-247 AD



G = Gate,
E = Emitter,

C = Collector,
TAB = Collector

Features

- International standard packages
JEDEC TO-247 SMD surface mountable and JEDEC TO-247 AD
- High frequency IGBT and anti-parallel FRED in one package
- 2nd generation HDMOS™ process
- Low $V_{CE(sat)}$
 - for minimum on-state conduction losses
- MOS Gate turn-on
 - drive simplicity
- Fast Recovery Epitaxial Diode (FRED)
 - soft recovery with low I_{RM}

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages

- Space savings (two devices in one package)
- Suitable for surface mounting
- Easy to mount with 1 screw, TO-247 (isolated mounting screw hole)
- Reduces assembly time and cost

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 750\ \mu\text{A}$, $V_{GE} = 0\text{ V}$	600		V
$V_{GE(th)}$	$I_C = 1.5\text{ mA}$, $V_{CE} = V_{GE}$	3.5		V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0\text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			500 μA 8 mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$ IXSH 24N60U1 IXSH 24N60AU1			2.2 V 2.7 V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}, V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	9	13	S
$I_{C(on)}$	$V_{GE} = 15\text{ V}$, $V_{CE} = 10\text{ V}$		65	A
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		1800	pF
C_{oes}			200	pF
C_{res}			45	pF
Q_g	$I_C = I_{C90}, V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		75	nC
Q_{ge}			20	nC
Q_{gc}			35	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 10\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		100	ns
t_{ri}			200	ns
$t_{d(off)}$			450	ns
t_{fi}		24N60U1	500	ns
E_{off}		24N60AU1	275	ns
		24N60AU1	2	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 10\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		100	ns
t_{ri}			200	ns
E_{on}			1.8	mJ
$t_{d(off)}$			475	ns
t_{fi}		24N60U1	600	ns
		24N60AU1	450	ns
E_{off}		24N60U1	4	mJ
		24N60AU1	3	mJ
R_{thJC}				0.83 K/W
R_{thCK}			0.25	K/W

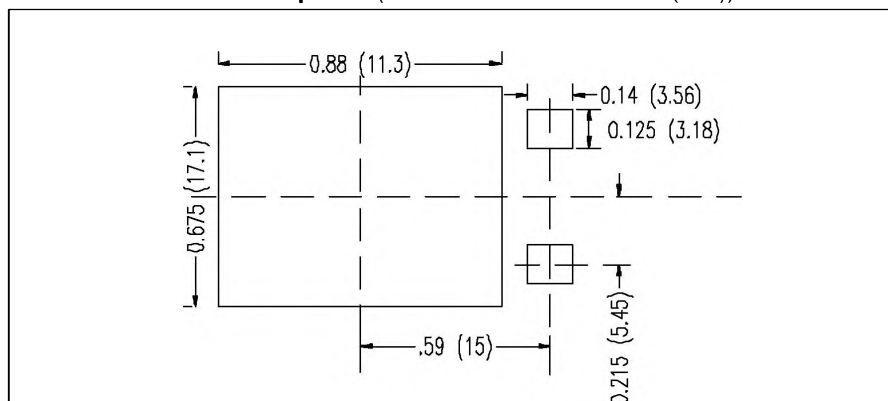
Reverse Diode (FRED)

Characteristic Values

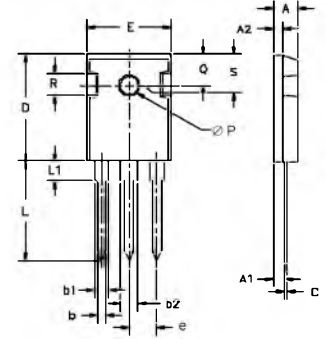
(T_J = 25°C, unless otherwise specified)

Symbol	Test Conditions	min.	typ.	max.
V_F	$I_F = I_{C90}, V_{GE} = 0\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$			1.6 V
I_{RM}	$I_F = I_{C90}, V_{GE} = 0\text{ V}$, $-di_F/dt = 240\text{ A}/\mu\text{s}$ $V_R = 360\text{ V}$ $I_F = 1\text{ A}$; $-di_F/dt = 100\text{ A}/\mu\text{s}$; $V_R = 30\text{ V}$		10	A
t_{rr}		$T_J = 125^\circ\text{C}$	150	ns
		$T_J = 25^\circ\text{C}$	35	ns
R_{thJC}				1 K/W

Min. Recommended Footprint (Dimensions in inches and (mm))

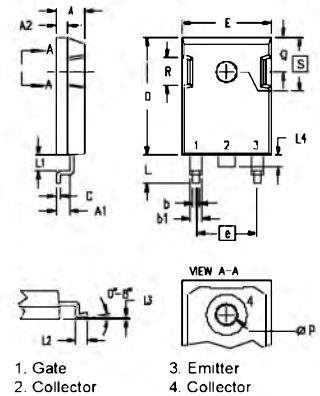


TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-247 SMD Outline

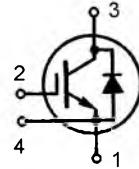


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45	BSC	.215	BSC
L	4.90	5.10	.193	.201
L ₁	2.70	2.90	.106	.114
L ₂	2.10	2.30	.083	.091
L ₃	0.00	0.10	.00	.004
L ₄	1.90	2.10	.075	.083
ØP	3.55	3.65	.140	.144
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190
S	6.15	BSC	.242	BSC

High Voltage IGBT with Diode

IXSN 35N120AU1

$$\begin{aligned} V_{CES} &= 1200 \text{ V} \\ I_{C25} &= 70 \text{ A} \\ V_{CE(sat)} &= 4 \text{ V} \end{aligned}$$

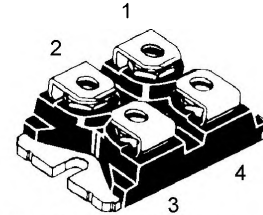


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	1200	A
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	70	A
I_{C90}	$T_C = 90^\circ\text{C}$	35	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	140	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 22 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 70$ @ $0.8 V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = 15 \text{ V}$, $V_{CE} = 0.6 \cdot V_{CES}$, $T_J = 125^\circ\text{C}$ $R_G = 22 \Omega$, non repetitive	10	μs
P_C P_D	$T_C = 25^\circ\text{C}$	IGBT Diode	300 175 W W
V_{ISOL}	50/60 Hz $I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ min}$ $t = 1 \text{ s}$	2500 3000 V~ V~
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque Terminal connection torque (M4)	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
Weight		30	g

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 5 \text{ mA}$, $V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 4 \text{ mA}$, $V_{CE} = V_{GE}$	4		V
I_{CES} ①	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$			$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$ 750 15 μA mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			± 100 nA
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15 \text{ V}$			4 V

① Device must be heat sunk during high temperature leakage test to avoid thermal runaway.

miniBLOC, SOT-227 B



1 = Emitter ①, 3 = Collector
2 = Gate, 4 = Emitter ①

① Either Emitter terminal can be used as Main or Kelvin Emitter

Features

- International standard package miniBLOC (ISOTOP) compatible
- Aluminium-nitride isolation
 - high power dissipation
- Isolation voltage 3000 V~
- Low $V_{CE(sat)}$
 - for minimum on-state conduction losses
- Fast Recovery Epitaxial Diode
 - short t_{rr} and I_{RM}
- Low collector-to-case capacitance (< 50 pF)
 - reducesd RFI
- Low package inductance (< 10 nH)
 - easy to drive and to protect

Applications

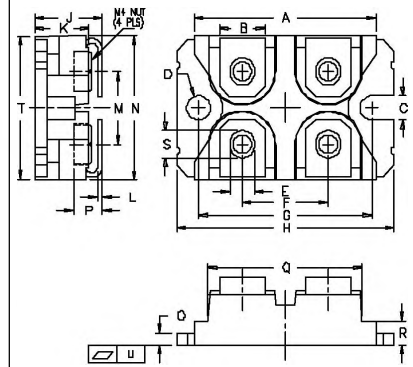
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages

- Space savings
- Easy to mount with 2 screws
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90^\circ}$, $V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$	20	26	S
$I_{C(on)}$	$V_{CE} = 10\text{ V}$, $V_{GE} = 15\text{ V}$		170	A
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		3900	pF
C_{oes}			295	pF
C_{res}			60	pF
Q_g	$I_C = I_{C90^\circ}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		150	nC
Q_{ge}			40	nC
Q_{gc}			70	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90^\circ}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.8 \cdot V_{CES}$, $R_G = 2.7\text{ }\Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G		80	ns
t_{rl}			150	ns
$t_{d(off)}$			400	900 ns
t_{fi}			500	700 ns
E_{off}			10	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90^\circ}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.8 \cdot V_{CES}$, $R_G = 2.7\text{ }\Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G		80	ns
t_{rl}			150	ns
$t_{d(off)}$			400	ns
t_{fi}			700	ns
E_{on}			6	mJ
E_{off}			15	mJ
R_{thJC}				0.42 K/W
R_{thCK}			0.05	K/W

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Reverse Diode (FRED)

Characteristic Values

($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions	min.	typ.	max.
V_F	$I_F = I_{C90^\circ}$, $V_{GE} = 0\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$			2.35 V
I_{RM}	$I_F = I_{C90^\circ}$, $V_{GE} = 0\text{ V}$, $-di_F/dt = 480\text{ A}/\mu\text{s}$ $V_R = 540\text{ V}$, $T_J = 100^\circ\text{C}$ $I_F = 1\text{ A}$, $-di_F/dt = 200\text{ A}/\mu\text{s}$; $V_R = 30\text{ V}$, $T_J = 25^\circ\text{C}$		32	35 A
t_{rr}			225	ns
t_{rr}			40	60 ns
R_{thJC}				0.71 K/W

IXYS MOSFETs and IGBTs are covered by one of the following U.S. patents: 4,835,592 4,881,108 5,017,508 5,049,961 5,187,117 5,486,715 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

IXYS reserves the right to change limits, test conditions, and dimensions.

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Fig. 1 Saturation Characteristics

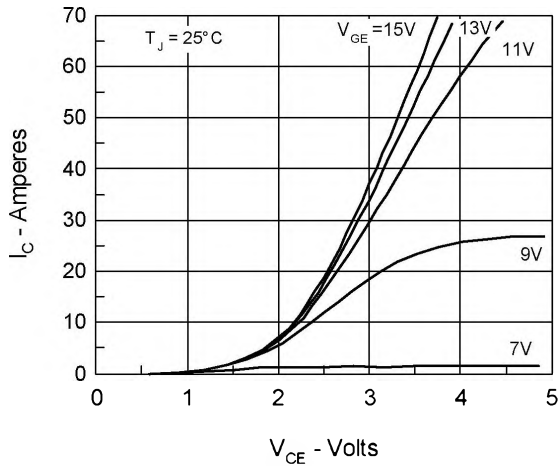


Fig. 2 Output Characteristics

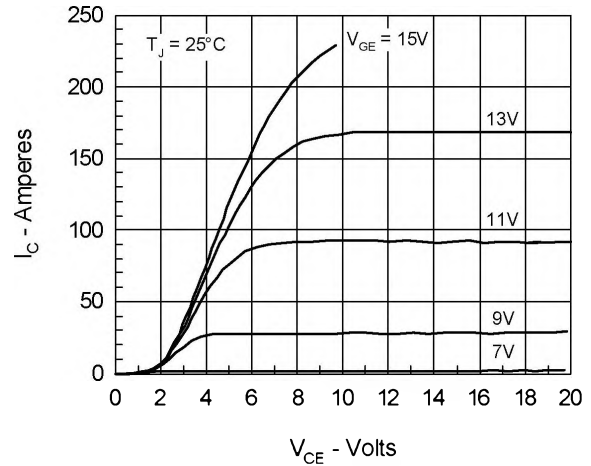


Fig. 3 Collector-Emitter Voltage vs. Gate-Emitter Voltage

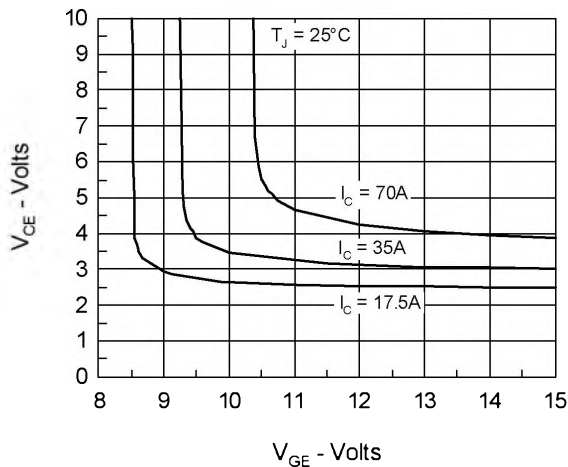


Fig. 4 Temperature Dependence of Output Saturation Voltage

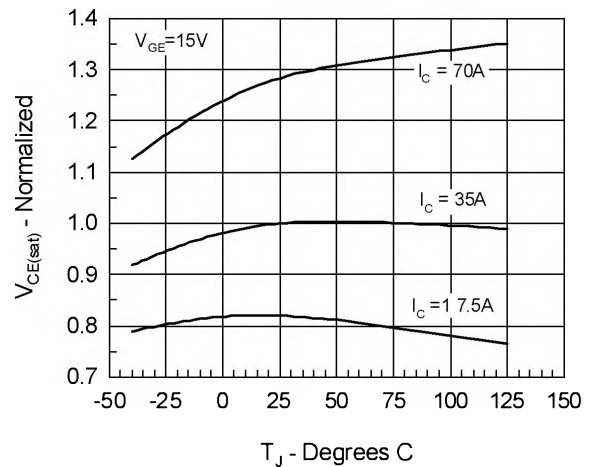


Fig. 5 Input Admittance

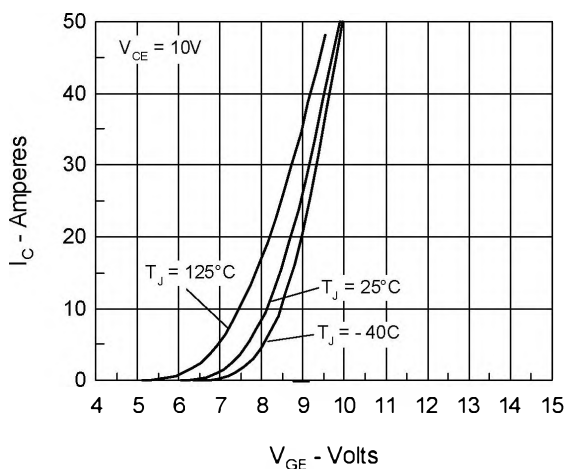


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

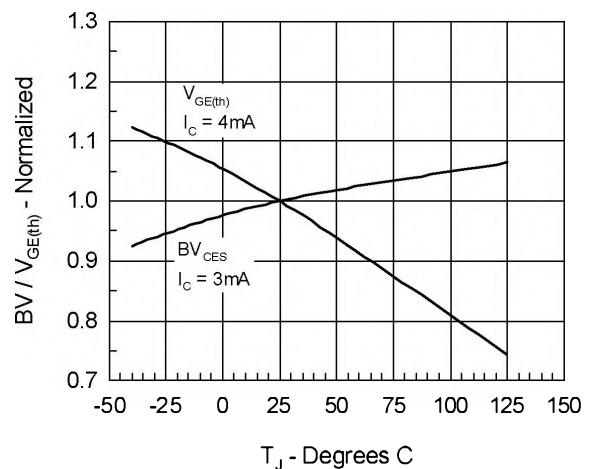
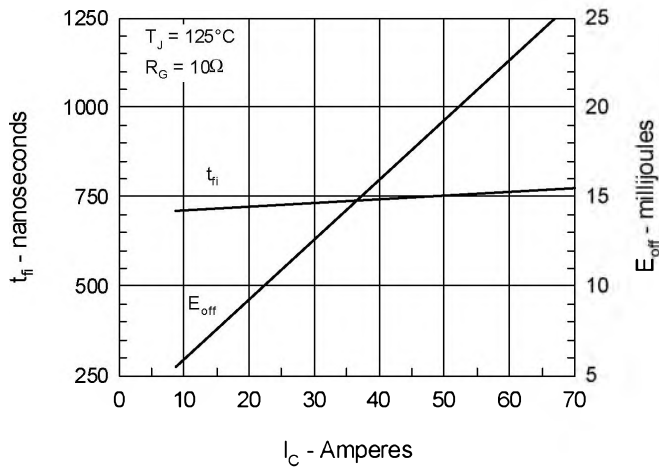
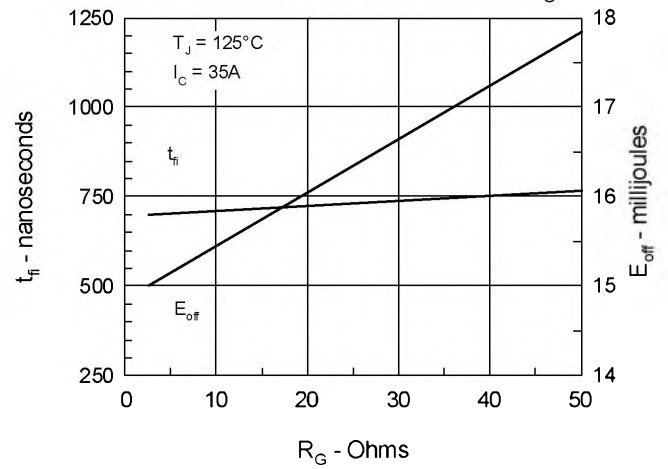
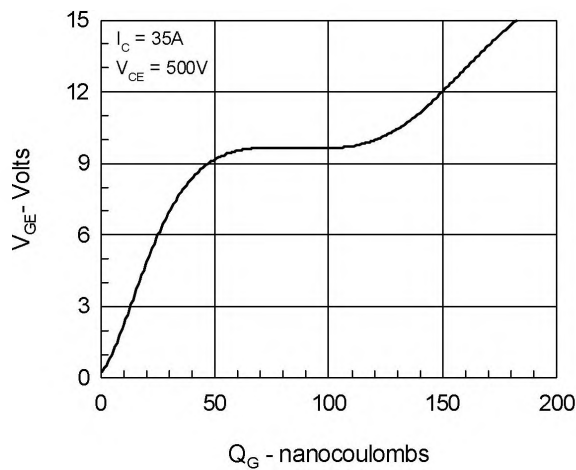
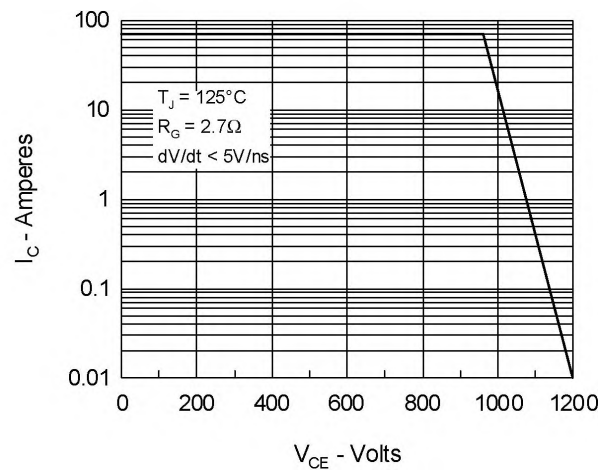
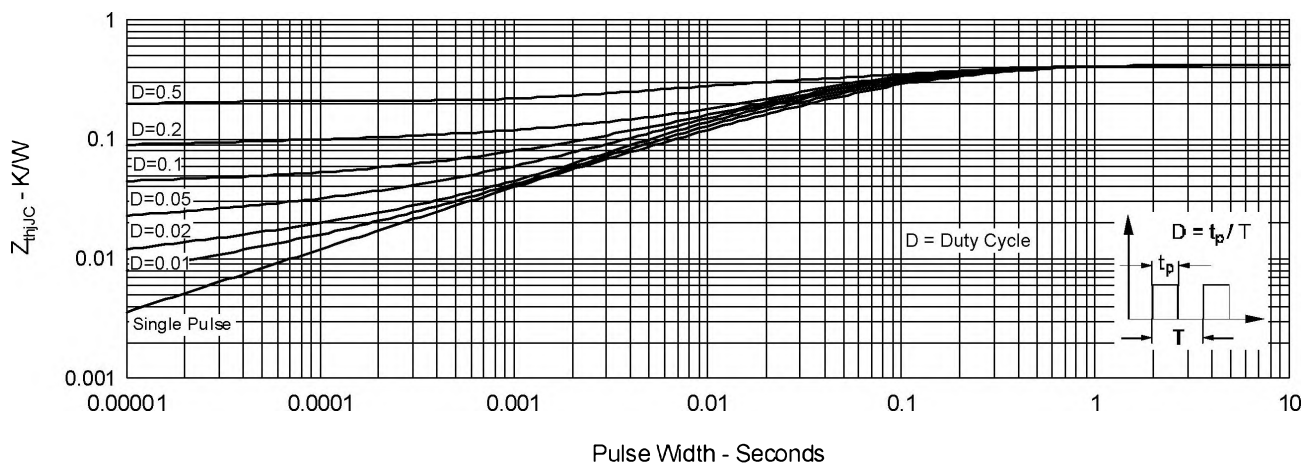


Fig.7 Turn-Off Energy per Pulse and Fall Time on Collector Current

Fig.8 Dependence of Turn-Off Energy Per Pulse and Fall Time on R_G

Fig.9 Gate Charge Characteristic Curve

Fig.10 Turn-Off Safe Operating Area

Fig.11 Transient Thermal Impedance


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